



《风光欣》技术资料

A928

PNP EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPIFIER

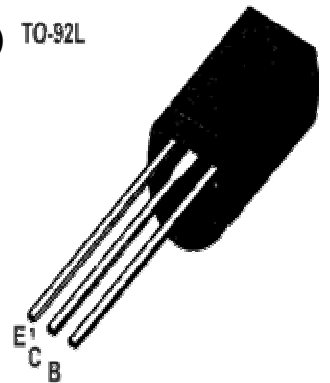
*Complement to C2328

*Collector Dissipation $P_c=1W$

*3Watt Output Application

ABSOLUTE MAXIMUM RATINGS(TA=25) TO-92L

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter -Base Voltage	V_{EBO}	-5	V
Collector Current	I_c	-2	A
Collector Dissipation	P_c	1	W
Junction Temperature	T_j	150	
Storage Temperature	T_{STG}	-55 ~ +150	



ELECTRICAL CHARACTERISTICS(TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = -100 \mu A, I_E = 0$	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = -10mA, I_B = 0$	-30			V
Emitter -Base Breakdown Voltage	BV_{EBO}	$I_E = -1mA, I_c = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_c = 0,$			-100	nA
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_c = -500mA,$	100		320	
Base-Emitter On Voltage	$V_{BE(on)}$	$V_{CE} = -2V, I_c = -500mA$			-1	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -1.5A, I_B = -30mA$			-2	V
Output Capacitance	C_{OB}	$V_{CB} = -10V, I_E = 0, F = 1MHZ$		48		pF
Current Gain -Bandwidth product	f_T	$V_{CE} = -2V, I_c = -500mA$		120		MHZ

hfe CLASSIFICATION

Classification	O	Y
h_{FE}	100~200	160~320